

Method of manufacturing a semiconductor device

Publication number: TW511188B

Publication date: 2002-11-21

Inventor: TOHDA TOSHIYUKI (JP); ARII ISAKU (JP)

Applicant: SHARP KK (JP)

Classification:

- international: H01L21/302; H01L21/3065; H01L21/311; H01L21/768;
H01L21/02; H01L21/70; (IPC1-7): H01L21/3205;
H01L21/3213

- European: H01L21/311B2B; H01L21/311B2B2; H01L21/768B2

Application number: TW20010118076 20010724

Priority number(s): JP20000222703 20000724

Also published as:



US6613680 (B2)

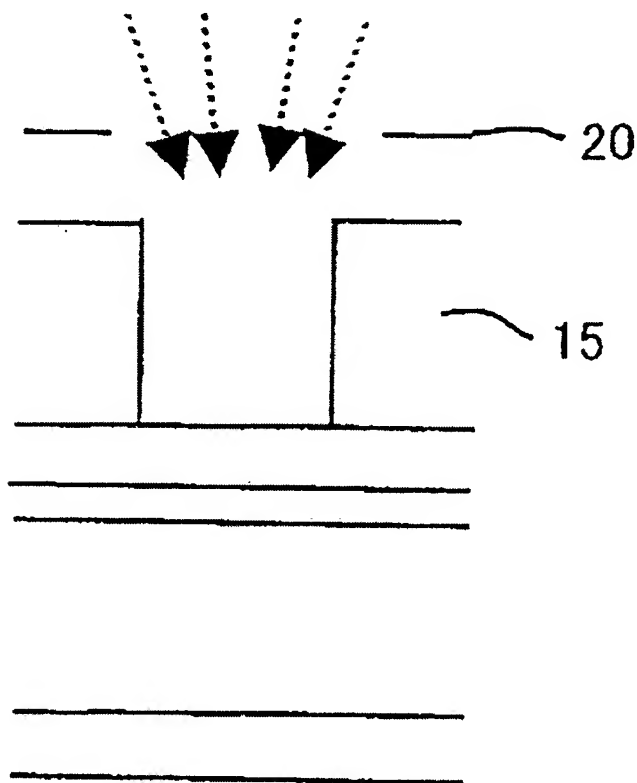
US2002039837 (A1)

JP2002043421 (A)

[Report a data error here](#)

Abstract of TW511188B

A method of manufacturing a semiconductor device provided with a first insulating film and a barrier film on a conductive region and an opening portion in the first insulating film and the barrier film, the method comprising the steps of: forming a first opening portion in the barrier film reaching the first insulating film; forming a second insulating film at least on the first insulating film in the first opening portion; and forming a second opening portion smaller than the first opening portion and reaching the conductive region by simultaneously boring a hole into the first insulating film and the second insulating film in the first opening portion.



Data supplied from the esp@cenet database - Worldwide